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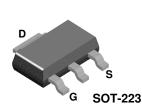
FQT13N06 N-Channel QFET[®] MOSFET 60 V, 2.8 A, 140 mΩ

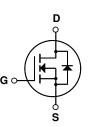
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 2.8 A, 60 V, $R_{DS(on)}$ =140 m Ω (Max.) @V_{GS}=10 V, I_D=1.4 A
- Low Gate Charge (Typ. 5.8 nC)
- Low Crss (Typ. 15 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted

Symbol	Parameter		FQT13N06	Unit
V _{DSS}	Drain-Source Voltage		60	V
I _D	Drain Current - Continuous (T _C = 25	°C)	2.8	А
	- Continuous (T _C = 70°C)		2.24	А
I _{DM}	Drain Current - Pulsed	(Note 1)	11.2	А
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	85	mJ
I _{AR}	Avalanche Current	(Note 1)	2.8	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	0.21	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		2.1	W
	- Derate above 25°C		0.017	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

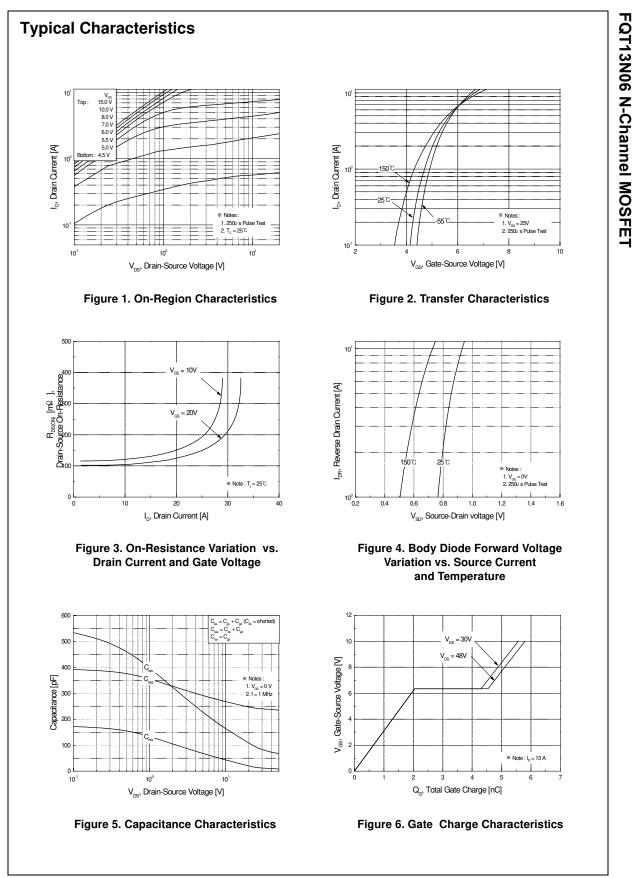
Symbol	Parameter	Тур	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *		60	°C/W



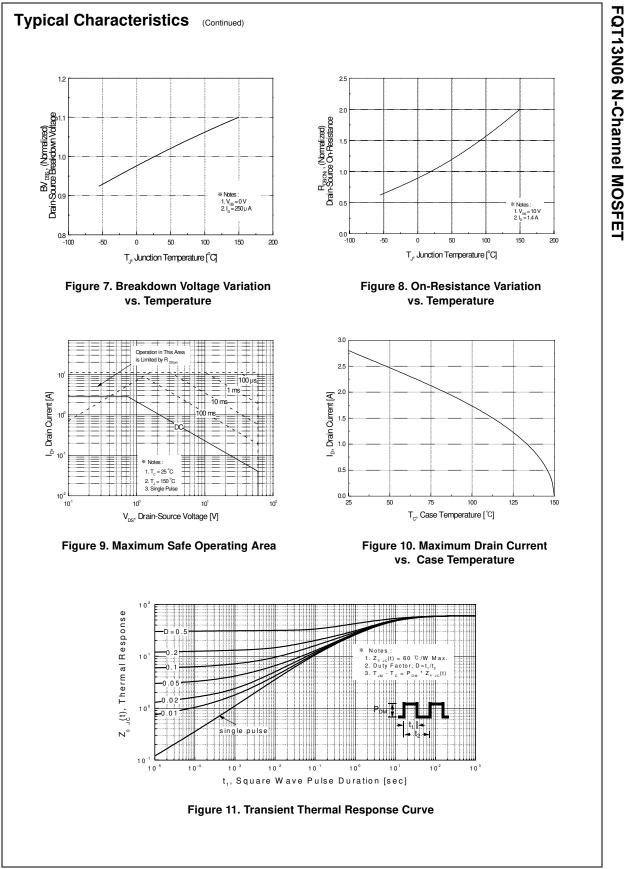
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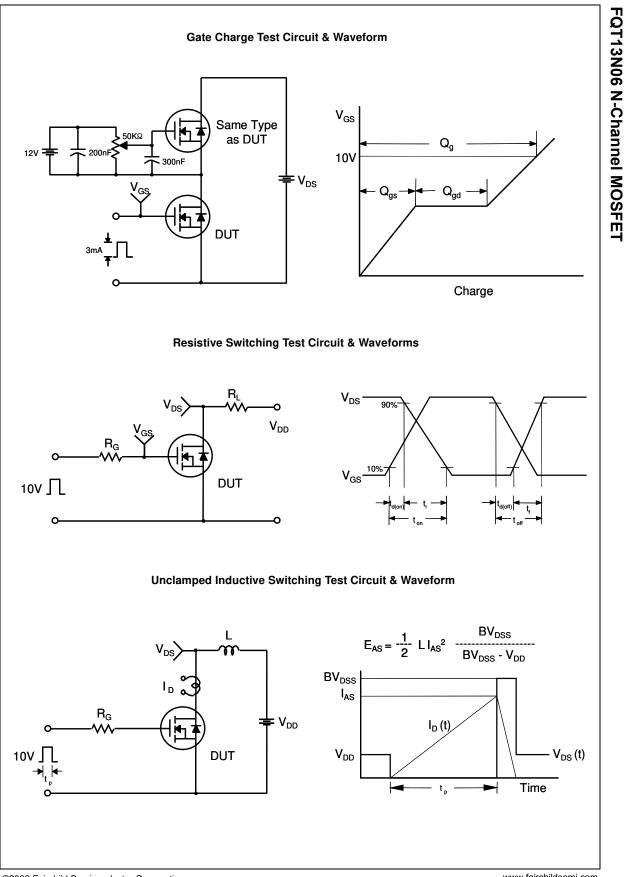
Acteristics Drain-Source Breakdown Voltage Breakdown Voltage Temperature					
Drain-Source Breakdown Voltage Breakdown Voltage Temperature					
Breakdown Voltage Temperature					V
3	$V_{GS} = 0 V$, $I_D = 250 \mu A$ $I_D = 250 \mu A$, Referenced to				V
Coefficient	$D = 250 \mu\text{A}$, hereferenced to 25°C		0.06		V/°C
	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$			10	μA
Gate-Body Leakage Current, Forward	$V_{GS} = 25 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			100	nA
Gate-Body Leakage Current, Reverse	$V_{GS} = -25 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			-100	nA
atariatian					
	$V_{22} = V_{22}$ $l_{2} = 250 \mu$	2.0		4.0	V
					ν Ω
					S
			0.0		Ŭ
Characteristics					
nput Capacitance	$V_{DS} = 25 V, V_{GS} = 0 V,$		240	310	pF
Dutput Capacitance	f = 1.0 MHz		90	120	pF
Reverse Transfer Capacitance			15	20	pF
n Characteristics					
			5	20	ns
	$V_{DD} = 30 \text{ V}, \text{ I}_{D} = 6.5 \text{ A},$				ns
	$R_{G} = 25 \Omega$				ns
Turn-Off Fall Time	(Note 4, 5)		15	40	ns
Total Gate Charge	$V_{DS} = 48 V. I_{D} = 13 A.$		5.8	7.5	nC
Gate-Source Charge	50 5		2.0		nC
Gate-Drain Charge	(Note 4, 5)		2.5		nC
uran Diado Characteristico er	d Movimum Dotingo				
				20	۸
					A A
					V
					ns
,	$dI_{\rm F} / dt = 100 \text{ A/}\mu \text{s}$ (Note 4)		40		nC
	Characteristics Curn-On Delay Time Curn-Off Delay Time Curn-Off Fall Time Cotal Gate Charge Chate-Source Charge Characteristics Characteristics Characteristics Characteristics Curn-Off Fall Time Cotal Gate Charge Characteristics Characteristics Characteristics Characteristics Characteristics Curn-Off Fall Time Cotal Gate Charge Characteristics Characteristics Characteristics Characteristics Characteristics Characteristics Curn-Off Fall Time Cotal Gate Charge Characteristics	Bate-Body Leakage Current, Forward $V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$ Bate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ Interstics $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ Bate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{A}$ Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 1.4 \text{ A}$ Forward Transconductance $V_{DS} = 25 \text{ V}, I_D = 1.4 \text{ A}$ Characteristics $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_S = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_S = 1.0 \text{ MHz}$ Characteristics $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_S = 1.0 \text{ MHz}$ Characteristics $V_{DD} = 30 \text{ V}, I_D = 6.5 \text{ A}, I_S = 25 \Omega$ Turn-On Delay Time $V_{DD} = 30 \text{ V}, I_D = 6.5 \text{ A}, I_G = 25 \Omega$ Turn-Off Delay Time $V_{DS} = 48 \text{ V}, I_D = 13 \text{ A}, I_S = 25 \Omega$ Turn-Off Fall Time $V_{GS} = 10 \text{ V}$ Chate-Source Charge $V_{GS} = 10 \text{ V}$ Characteristics and Maximum RatingsMaximum Continuous Drain-Source Diode Forward CurrentMaximum Pulsed Drain-Source Diode Forward CurrentCharacteristics Reverse Recovery TimeVGS = 0 V, I_S = 13 A, I_S = 13 A	Bate-Body Leakage Current, Forward $V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$ Bate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ CeteristicsBate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{A}$ 2.0Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 1.4 \text{ A}$ Forward Transconductance $V_{DS} = 25 \text{ V}, I_D = 1.4 \text{ A}$ Characteristics $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_D = 1.4 \text{ A}$ Characteristics $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_D = 1.4 \text{ A}$ Dutput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_D = 1.4 \text{ A}$ Output Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_D = 1.4 \text{ A}$ Purn-On Delay Time $V_{DD} = 30 \text{ V}, I_D = 6.5 \text{ A}, I_D = -1.4 \text{ A}$ Turn-On Delay Time $V_{DS} = 30 \text{ V}, I_D = 6.5 \text{ A}, I_D = -1.4 \text{ A}$ Turn-Off Delay Time $V_{DS} = 10 \text{ V}, I_D = 1.3 \text{ A}, I_D = -1.4 \text{ A}$ Turn-Off Fall Time $V_{DS} = 48 \text{ V}, I_D = 13 \text{ A}, I_D = -1.4 \text{ A}$ Turn-Off Characteristics and Maximum RatingsAaximum Continuous Drain-Source Diode Forward CurrentAximum Pulsed Drain-Source Diode Forward CurrentAximum Pulsed Drain-Source Diode Forward Current $V_{GS} = 0 \text{ V}, I_S = 13 \text{ A}, I_D$ Prain-Source Diode Forward Voltage $V_{GS} = 0 \text{ V}, I_S = 13 \text{ A}, I_D$	Bate-Body Leakage Current, Forward $V_{GS} = 25 V, V_{DS} = 0 V$ Bate-Body Leakage Current, Reverse $V_{GS} = -25 V, V_{DS} = 0 V$ InteristicsBate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu A$ 2.0Static Drain-Source On-Resistance $V_{GS} = 10 V, I_D = 1.4 A$ 0.11Forward Transconductance $V_{DS} = 25 V, V_{GS} = 0 V,$ 3.0Characteristicsmput Capacitance $V_{DS} = 25 V, V_{GS} = 0 V,$ 240Dutput Capacitance $V_{DS} = 25 V, V_{GS} = 0 V,$ 90Reverse Transfer Capacitance $V_{DD} = 30 V, I_D = 6.5 A,$ 5urn-On Delay Time $V_{DD} = 30 V, I_D = 6.5 A,$ 5urn-Off Delay Time $V_{DS} = 48 V, I_D = 13 A,$ 5.8urn-Off Fall Time $V_{GS} = 10 V$ 2.0State-Source Charge $V_{GS} = 10 V$ 2.5urce Diode Characteristics and Maximum RatingsMaximum Continuous Drain-Source Diode Forward Current $P_{GS} = 0 V, I_S = 2.8 A$ $P_{GS} = 0 V, I_S = 13 A,$ </td <td>Bate-Body Leakage Current, Forward $V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$ 100 Bate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ 100 Interistics Bate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{ A}$ 2.0 4.0 Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 1.4 \text{ A}$ 0.11 0.14 forward Transconductance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_D = 1.4 \text{ A}$ 0.11 0.14 forward Transconductance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_D = 1.4 \text{ A}$ 0.11 0.14 forward Transconductance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_D = 1.4 \text{ A}$ 0.01 Characteristics mput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_D = 1.2 \text{ A}, I_D$</td>	Bate-Body Leakage Current, Forward $V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$ 100 Bate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ 100 Interistics Bate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{ A}$ 2.0 4.0 Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 1.4 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FQT13N06 N-Channel MOSFET



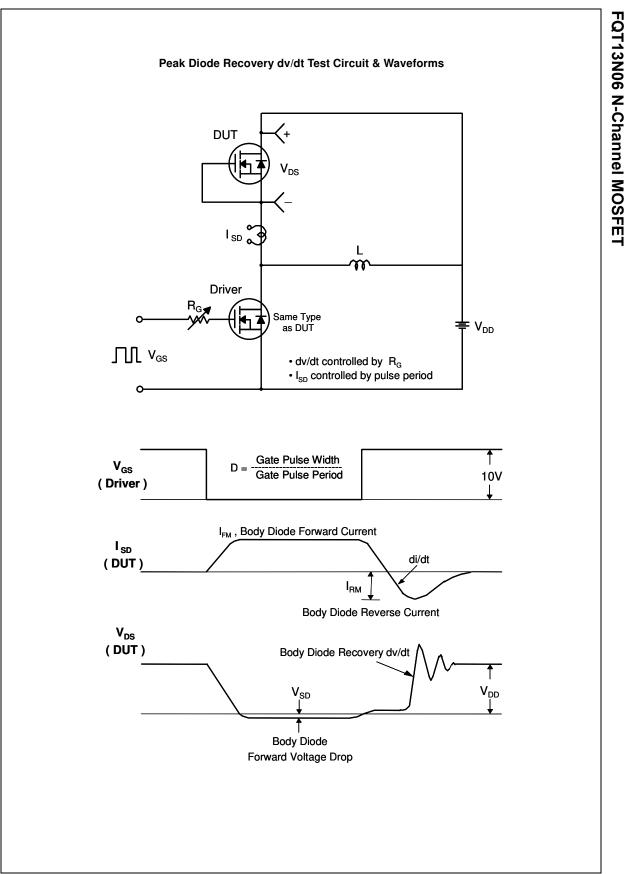
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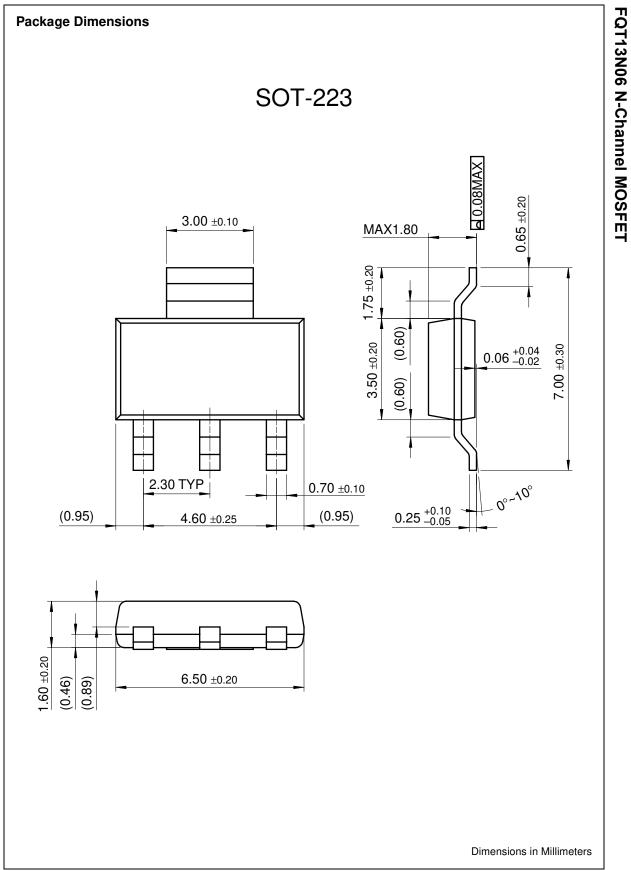




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